

MD2103DFP

High voltage NPN power transistor for standard definition CRT display

Features

- State-of-the-art technology:
 - Diffused collector "enhanced generation"
- Stable performance versus operating temperature variation
- Low base drive requirement
- Tight h_{FE} range at operating collector current
- Fully insulated power package UL compliant
- Integrated free wheeling diode



■ Horizontal deflection output for TV



The MD2103DFP is manufactured using diffused collector in planar technology adopting new and enhanced high voltage structure. The new MD product series show improved silicon efficiency briging updated performance to the horizontal deflection stage.

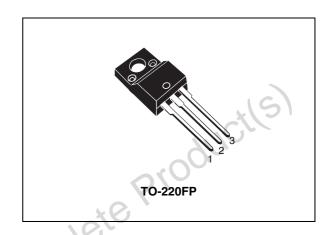


Figure 1. Internal schematic diagram $\begin{array}{c}
C \circ (2) \\
B \circ \\
R_{BE}=65\Omega \text{ (typ)}
\end{array}$ SC12350 E (3)

Table 1. Device summary

Order code	Marking	Package	Packing
MD2103DFP	MD2103DFP	TO-220FP	Tube

Electrical ratings MD2103DFP

1 Electrical ratings

Table 2. Absolute maximum rating

Symbol	Parameter	Value	Unit
V_{CES}	Collector-emitter voltage (V _{BE} =0)	1500	V
V _{CEO}	Collector-emitter voltage (I _B =0)	700	V
V _{EBO}	Emitter-base voltage (I _C =0)	7	V
I _C	Collector current	6	Α
I _{CM}	Collector peak current (t _P < 5ms)	9 16	Α
Ι _Β	Base current	3	Α
P _{tot}	Total dissipation at T _c ⊴5°C	38	W
V _{INS}	Insulation withstand voltage (RMS) from all three leads to external heatsink		٧
T _{stg}	Storage temperature	-65 to 150	°C
T _J	Max. operating junction temperature	150	°C

Table 3. Thermal data

	Symbol	Parameter	Value	Unit °C/W	
	R _{thj-case}	Thermal resistance junction-case max	3.3		
		400	•	<u> </u>	
		100			
	V.C.Y				
16	3/6				
12501					
Op					

Electrical characteristics 2

(T_{case} = 25°C unless otherwise specified)

Electrical characteristics Table 4.

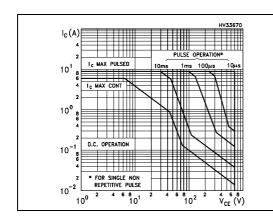
Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I _{CES}	Collector cut-off current (V _{BE} =0)	V _{CE} = 1500V V _{CE} = 1500V T _C = 125°C			0.2 2	mA mA
I _{EBO}	Emitter cut-off current (I _C =0)	V _{EB} = 5V	50		125	mA
V _{(BR)EBO}	Emitter-base brakdown voltage (I _C = 0)	I _E = 700mA		11		V
V _{CE(sat)} (1)	Collector-emitter saturation voltage	I _C = 3A I _B =0.75A	0),	0,0	1.8	V
V _{BE(sat)} (1)	Base-emitter saturation voltage	I _C = 3A I _B =0.75A			1.5	V
h _{FE} ⁽¹⁾	DC current gain	$\begin{split} I_{C} &= 1A & V_{CE} = 5V \\ I_{C} &= 3A & V_{CE} = 1V \\ I_{C} &= 3A & V_{CE} = 5V \end{split}$	6.5	17 6	9.5	
t _s	Inductive load Storage time Fall time	I_C =3A f_h =16kHz $I_{B(on)}$ =0.5A $V_{BE(off)}$ =-2.7V $L_{BB(off)}$ =6.3 μ H (see <i>Figure 12</i>)		3.8 0.25		μs μs
V _F	Diode forward voltage	I _F = 3A			2	٧
Note (1) Pul	lsed duration = 300 μs, d	uty cycle ≤1.5%				

Electrical characteristics MD2103DFP

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

Figure 3. Derating curve



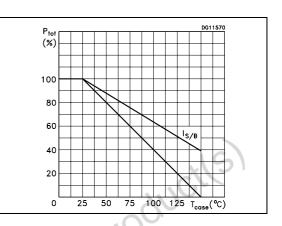
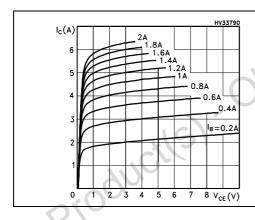


Figure 4. Output characteristics

Figure 5. Reverse biased SOA



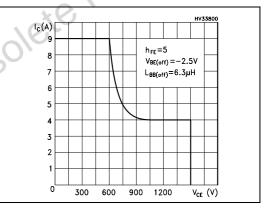
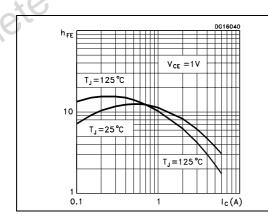


Figure 6. DC current gain

Figure 7. DC current gain



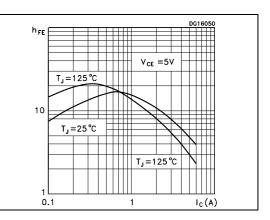


Figure 8. Collector-emitter saturation Figure 9. Base-emitter saturation voltage voltage

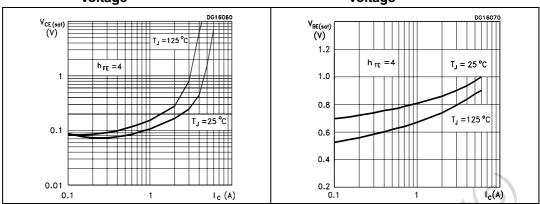
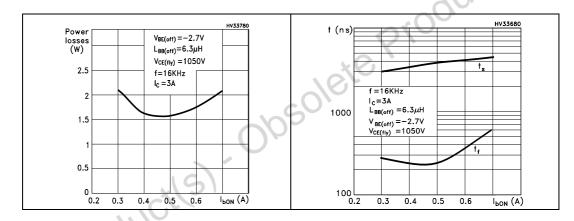


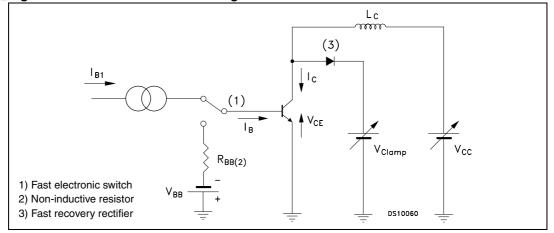
Figure 10. Power losses

Figure 11. Inductive load switching time



2.2 Test circuits

Figure 12. Inductive load switching test circuit



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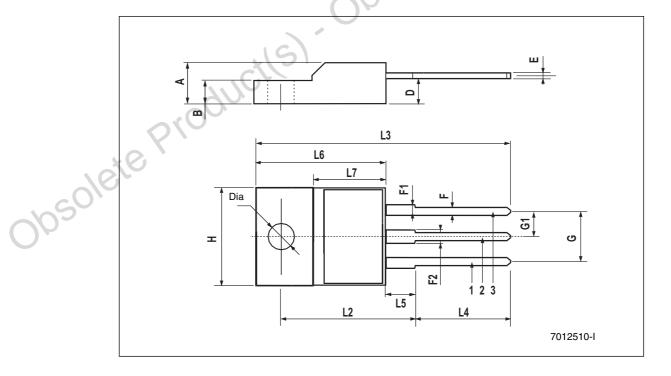
3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

Obsolete Product(s). Obsolete Product(s)

TO-220FP mechanical data

Dim.	mm.			inch		
	Min.	Тур	Max.	Min.	Тур.	Max.
Α	4.40		4.60	0.173		0.181
В	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
Е	0.45		0.70	0.017		0.027
F	0.75		1.00	0.030		0.039
F1	1.15		1.50	0.045		0.067
F2	1.15		1.50	0.045		0.067
G	4.95		5.20	0.195		0.204
G1	2.40		2.70	0.094		0.106
Н	10		10.40	0.393	. (0.409
L2		16			0.630	
L3	28.6		30.6	1.126	70	1.204
L4	9.80		10.60	0.385	$(\bigcirc$	0.417
L5	2.9		3.6	0.114		0.141
L6	15.90		16.40	0.626		0.645
L7	9		9.30	0.354		0.366
Dia	3		3.2	0.118		0.126



Revision history MD2103DFP

4 Revision history

Table 5. Document revision history

Date	Revision	Changes
27-May-2008	1	First release

Obsolete Product(s). Obsolete Product(s)

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